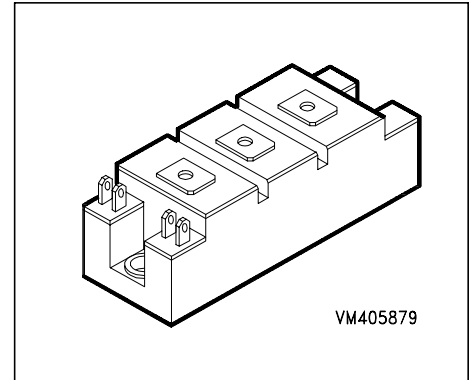


### IGBT Power Module

- Half-bridge
- Including fast free-wheeling diodes
- Package with insulated metal base plate



| Type              | $V_{CE}$ | $I_C$ | Package       | Ordering Code    |
|-------------------|----------|-------|---------------|------------------|
| BSM 50 GB 120 DN2 | 1200V    | 78A   | HALF-BRIDGE 1 | C67076-A2105-A70 |

### Maximum Ratings

| Parameter                                             | Symbol      | Values        | Unit             |
|-------------------------------------------------------|-------------|---------------|------------------|
| Collector-emitter voltage                             | $V_{CE}$    | 1200          | V                |
| Collector-gate voltage                                | $V_{CGR}$   | 1200          |                  |
| $R_{GE} = 20 \text{ k}\Omega$<br>Gate-emitter voltage | $V_{GE}$    | $\pm 20$      |                  |
| DC collector current                                  | $I_C$       | 78            | A                |
| $T_C = 25 \text{ }^\circ\text{C}$                     |             | 50            |                  |
| $T_C = 80 \text{ }^\circ\text{C}$                     |             |               |                  |
| Pulsed collector current, $t_p = 1 \text{ ms}$        | $I_{Cpuls}$ | 156           |                  |
| $T_C = 25 \text{ }^\circ\text{C}$                     |             | 100           |                  |
| $T_C = 80 \text{ }^\circ\text{C}$                     |             |               |                  |
| Power dissipation per IGBT                            | $P_{tot}$   | 400           | W                |
| $T_C = 25 \text{ }^\circ\text{C}$                     |             |               |                  |
| Chip temperature                                      | $T_j$       | + 150         | $^\circ\text{C}$ |
| Storage temperature                                   | $T_{stg}$   | -55 ... + 150 |                  |
| Thermal resistance, chip case                         | $R_{thJC}$  | $\leq 0.3$    | K/W              |
| Diode thermal resistance, chip case                   | $R_{thJCD}$ | $\leq 0.6$    |                  |
| Insulation test voltage, $t = 1\text{min.}$           | $V_{is}$    | 2500          | Vac              |
| Creepage distance                                     | -           | 20            | mm               |
| Clearance                                             | -           | 11            |                  |
| DIN humidity category, DIN 40 040                     | -           | F             | -                |
| IEC climatic category, DIN IEC 68-1                   | -           | 55 / 150 / 56 |                  |

### Electrical Characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

| Parameter | Symbol | Values |      |      | Unit |
|-----------|--------|--------|------|------|------|
|           |        | min.   | typ. | max. |      |

#### Static Characteristics

|                                                                                                                                                                                |               |        |            |          |    |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|--------|------------|----------|----|
| Gate threshold voltage<br>$V_{GE} = V_{CE}, I_C = 2\text{ mA}$                                                                                                                 | $V_{GE(th)}$  | 4.5    | 5.5        | 6.5      | V  |
| Collector-emitter saturation voltage<br>$V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_j = 25\text{ °C}$<br>$V_{GE} = 15\text{ V}, I_C = 50\text{ A}, T_j = 125\text{ °C}$        | $V_{CE(sat)}$ | -<br>- | 2.5<br>3.1 | 3<br>3.7 |    |
| Zero gate voltage collector current<br>$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$<br>$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$ | $I_{CES}$     | -<br>- | 0.8<br>3.5 | 1<br>-   | mA |
| Gate-emitter leakage current<br>$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$                                                                                                    | $I_{GES}$     | -      | -          | 200      |    |

#### AC Characteristics

|                                                                                               |           |    |      |   |    |
|-----------------------------------------------------------------------------------------------|-----------|----|------|---|----|
| Transconductance<br>$V_{CE} = 20\text{ V}, I_C = 50\text{ A}$                                 | $g_{fs}$  | 23 | -    | - | S  |
| Input capacitance<br>$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$            | $C_{iss}$ | -  | 3.3  | - | nF |
| Output capacitance<br>$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$           | $C_{oss}$ | -  | 0.5  | - |    |
| Reverse transfer capacitance<br>$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | $C_{rss}$ | -  | 0.25 | - |    |

### Electrical Characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

| Parameter | Symbol | Values |      |      | Unit |
|-----------|--------|--------|------|------|------|
|           |        | min.   | typ. | max. |      |

### Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

|                                                                                                                                 |              |   |     |     |    |
|---------------------------------------------------------------------------------------------------------------------------------|--------------|---|-----|-----|----|
| Turn-on delay time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 50\text{ A}$<br>$R_{Gon} = 22\text{ }\Omega$    | $t_{d(on)}$  | - | 44  | 100 | ns |
| Rise time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 50\text{ A}$<br>$R_{Gon} = 22\text{ }\Omega$             | $t_r$        | - | 56  | 100 |    |
| Turn-off delay time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = -15\text{ V}$ , $I_C = 50\text{ A}$<br>$R_{Goff} = 22\text{ }\Omega$ | $t_{d(off)}$ | - | 380 | 500 |    |
| Fall time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = -15\text{ V}$ , $I_C = 50\text{ A}$<br>$R_{Goff} = 22\text{ }\Omega$           | $t_f$        | - | 70  | 100 |    |

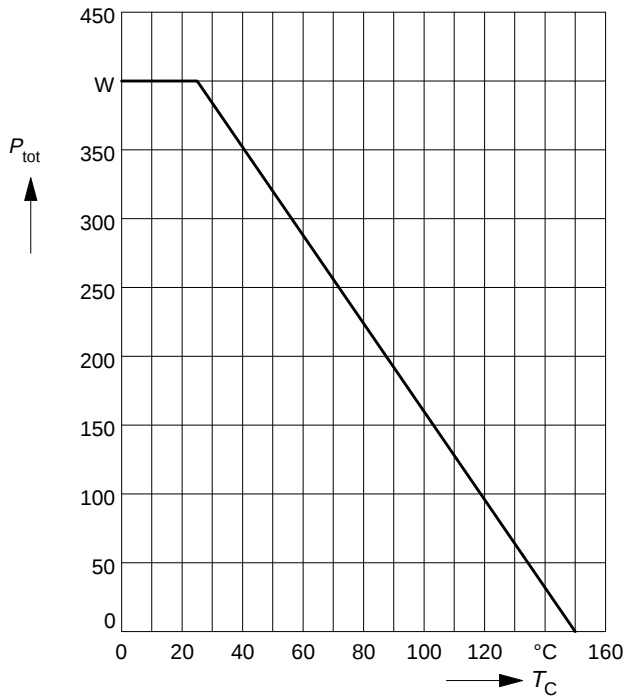
### Free-Wheel Diode

|                                                                                                                                                                                                                                                         |          |   |            |          |               |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|---|------------|----------|---------------|
| Diode forward voltage<br>$I_F = 50\text{ A}$ , $V_{GE} = 0\text{ V}$ , $T_j = 25\text{ °C}$<br>$I_F = 50\text{ A}$ , $V_{GE} = 0\text{ V}$ , $T_j = 125\text{ °C}$                                                                                      | $V_F$    | - | 2.3<br>1.8 | 2.8<br>- | V             |
| Reverse recovery time<br>$I_F = 50\text{ A}$ , $V_R = -600\text{ V}$ , $V_{GE} = 0\text{ V}$<br>$di_F/dt = -800\text{ A}/\mu\text{s}$ , $T_j = 125\text{ °C}$                                                                                           | $t_{rr}$ | - | 0.2        | -        |               |
| Reverse recovery charge<br>$I_F = 50\text{ A}$ , $V_{GE} = 0\text{ V}$<br>$V_R = -600\text{ V}$ , $di_F/dt = -800\text{ A}/\mu\text{s}$ , $T_j = 25\text{ °C}$<br>$V_R = -600\text{ V}$ , $di_F/dt = -800\text{ A}/\mu\text{s}$ , $T_j = 125\text{ °C}$ | $Q_{rr}$ | - | 2.8<br>8   | -<br>-   | $\mu\text{C}$ |
|                                                                                                                                                                                                                                                         |          | - |            |          |               |

### Power dissipation

$$P_{\text{tot}} = f(T_C)$$

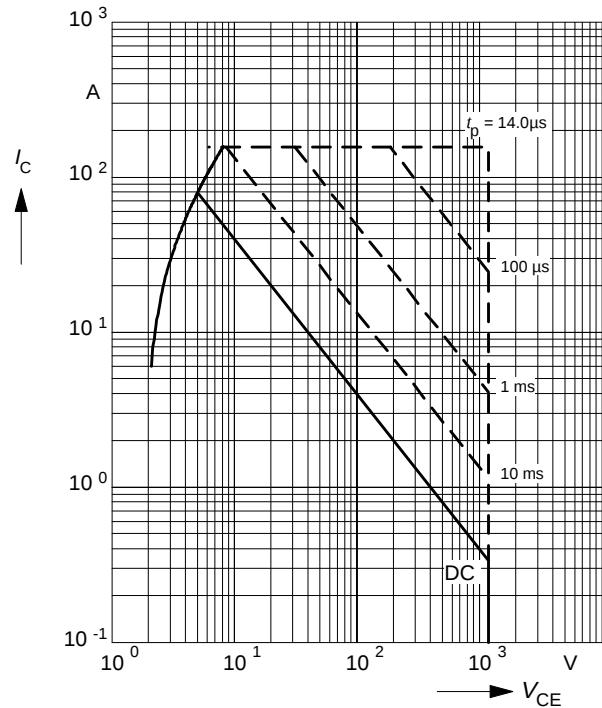
parameter:  $T_j \leq 150^\circ\text{C}$



### Safe operating area

$$I_C = f(V_{CE})$$

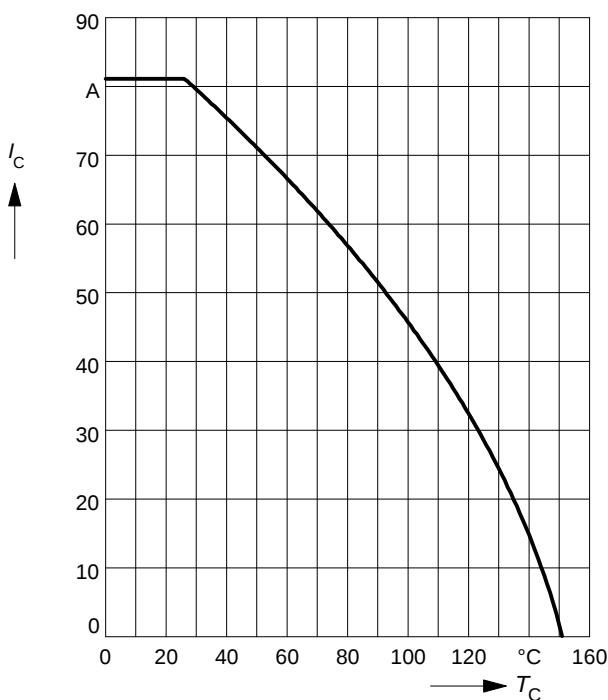
parameter:  $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$



### Collector current

$$I_C = f(T_C)$$

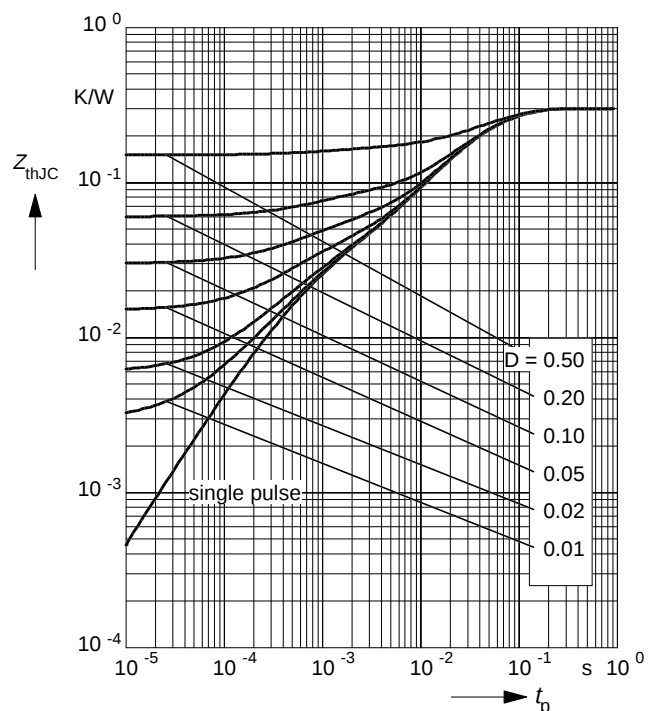
parameter:  $V_{GE} \geq 15\text{ V}$ ,  $T_j \leq 150^\circ\text{C}$



### Transient thermal impedance IGBT

$$Z_{\text{th JC}} = f(t_p)$$

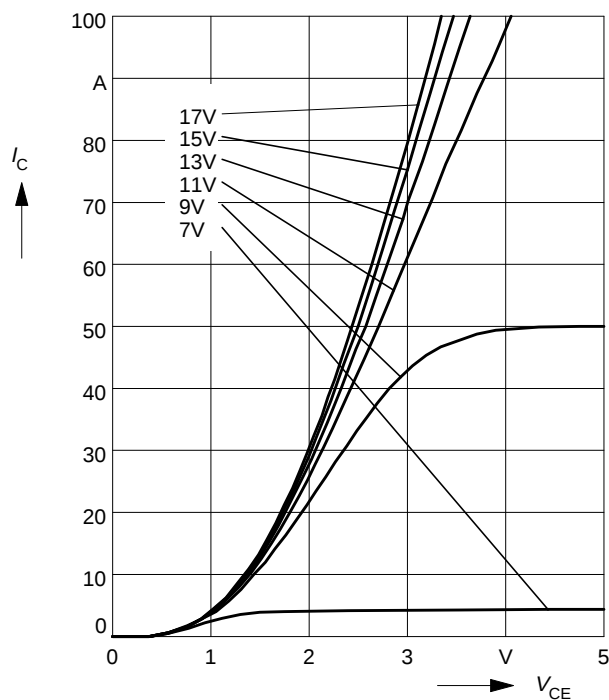
parameter:  $D = t_p / T$



### Typ. output characteristics

$$I_C = f(V_{CE})$$

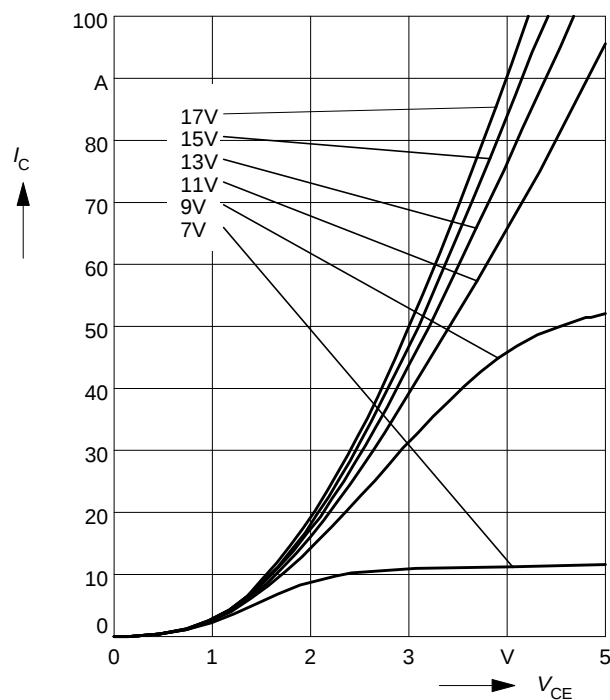
parameter:  $t_p = 80 \mu s$ ,  $T_j = 25^\circ C$



### Typ. output characteristics

$$I_C = f(V_{CE})$$

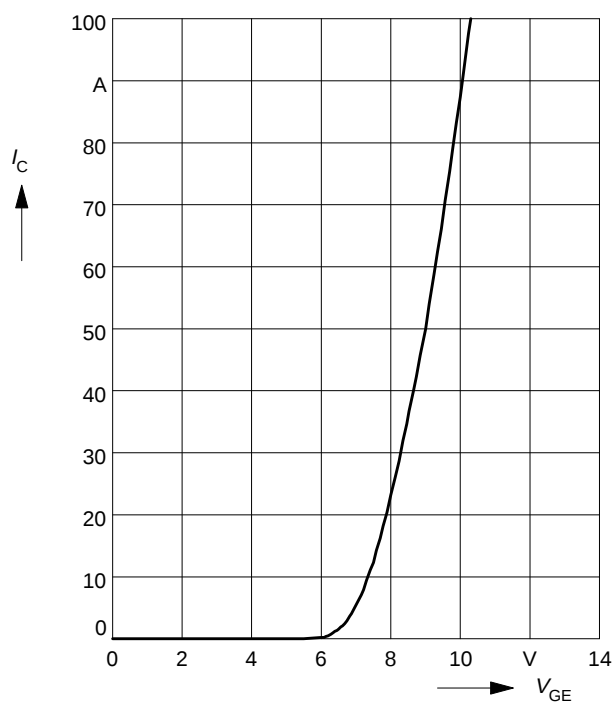
parameter:  $t_p = 80 \mu s$ ,  $T_j = 125^\circ C$



### Typ. transfer characteristics

$$I_C = f(V_{GE})$$

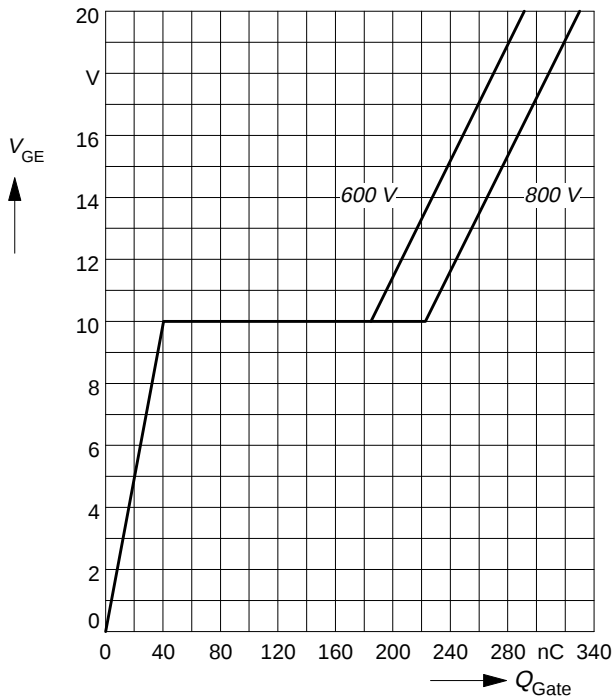
parameter:  $t_p = 80 \mu s$ ,  $V_{CE} = 20 V$



### Typ. gate charge

$$V_{GE} = f(Q_{Gate})$$

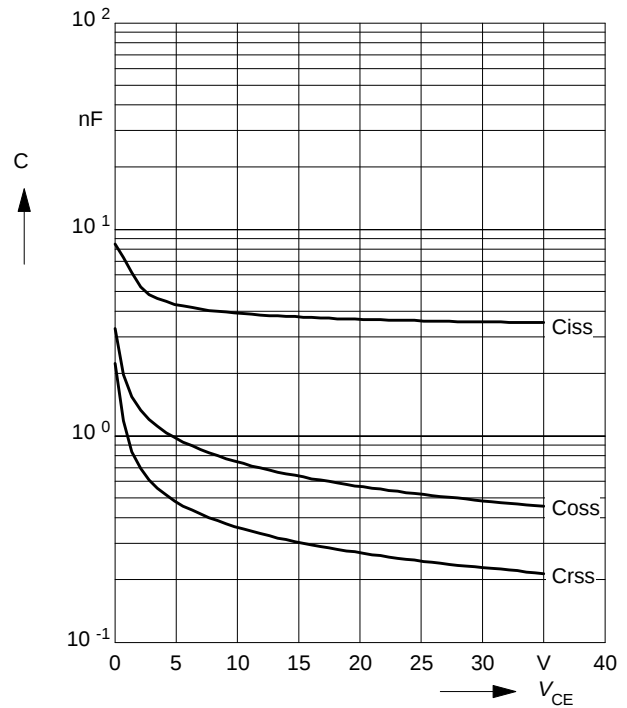
parameter:  $I_{C\ puls} = 50\ A$



### Typ. capacitances

$$C = f(V_{CE})$$

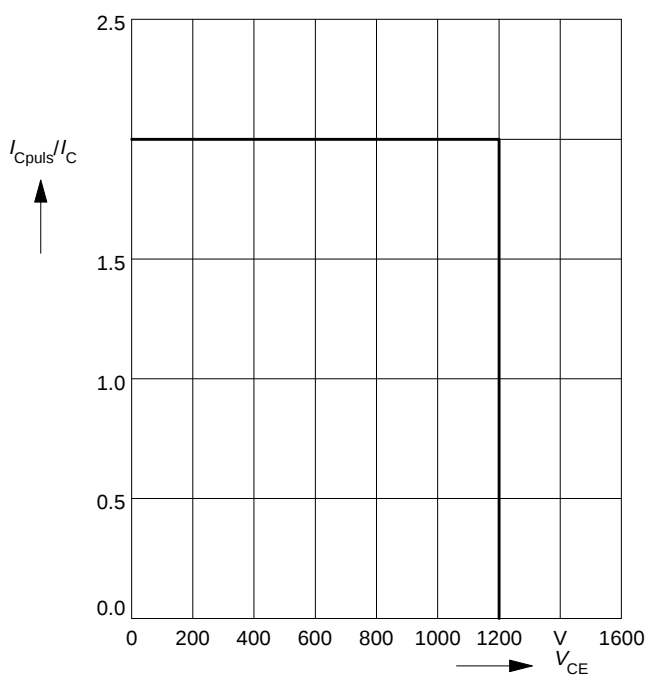
parameter:  $V_{GE} = 0, f = 1\ MHz$



### Reverse biased safe operating area

$$I_{C\ puls} = f(V_{CE}), T_j = 150^\circ C$$

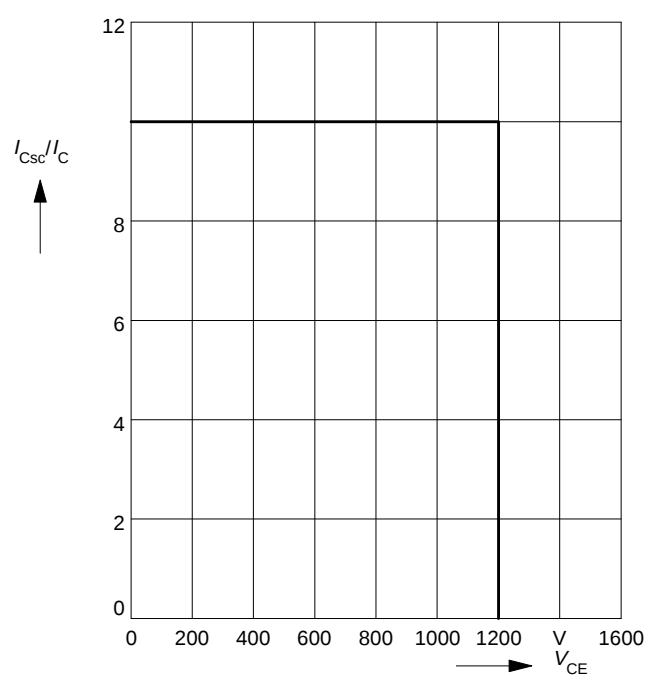
parameter:  $V_{GE} = 15\ V$



### Short circuit safe operating area

$$I_{C\ sc} = f(V_{CE}), T_j = 150^\circ C$$

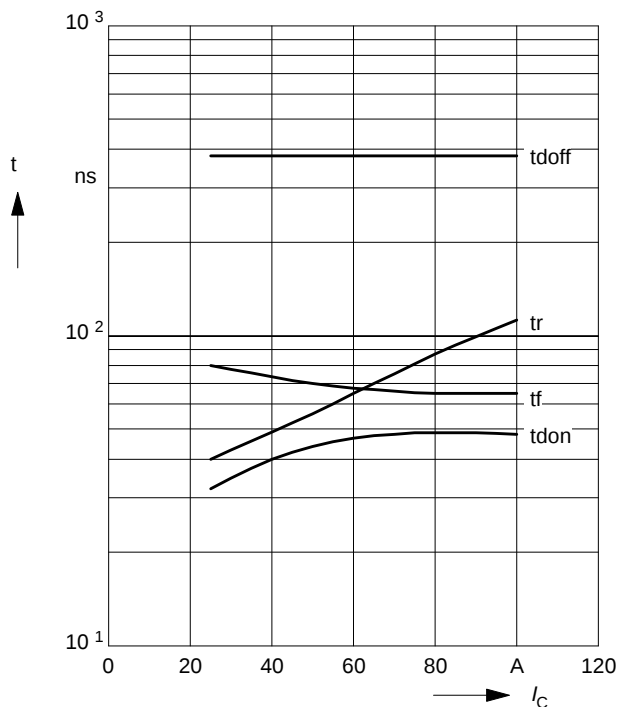
parameter:  $V_{GE} = \pm 15\ V, t_{SC} \leq 10\ \mu s, L < 50\ nH$



### Typ. switching time

$t = f(I_C)$ , inductive load,  $T_j = 125^\circ\text{C}$

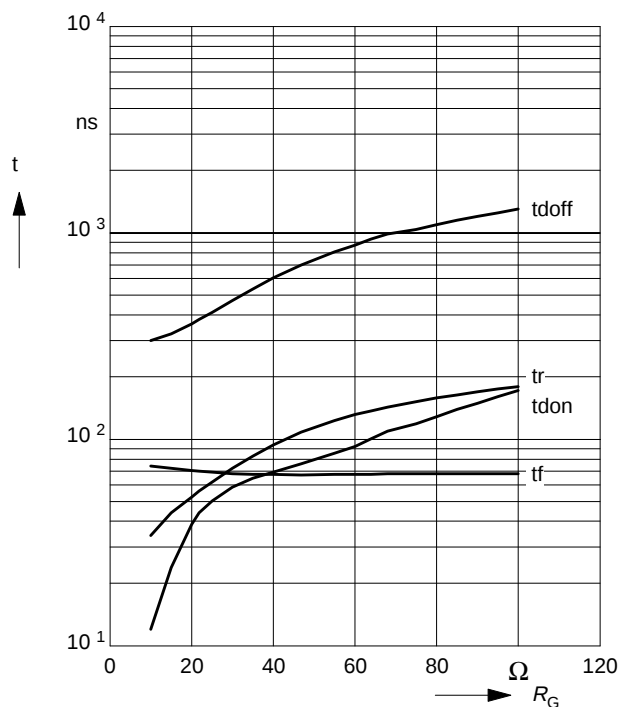
par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $R_G = 22\ \Omega$



### Typ. switching time

$t = f(R_G)$ , inductive load,  $T_j = 125^\circ\text{C}$

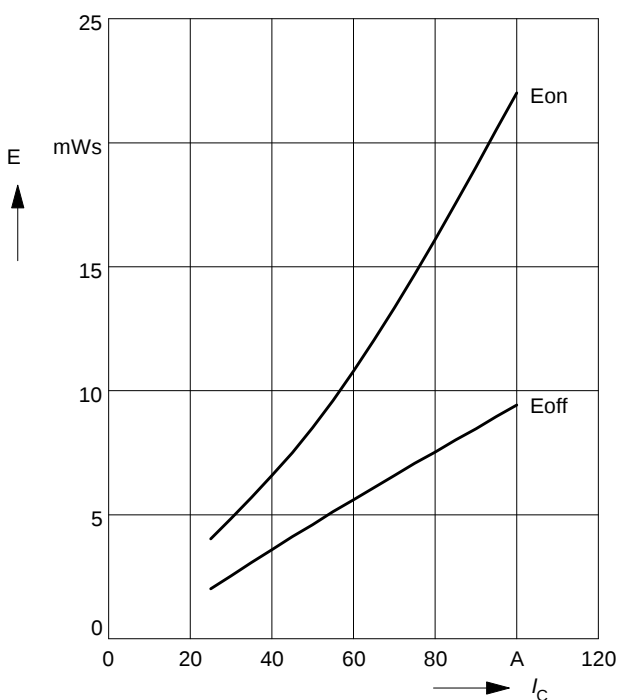
par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $I_C = 50\text{ A}$



### Typ. switching losses

$E = f(I_C)$ , inductive load,  $T_j = 125^\circ\text{C}$

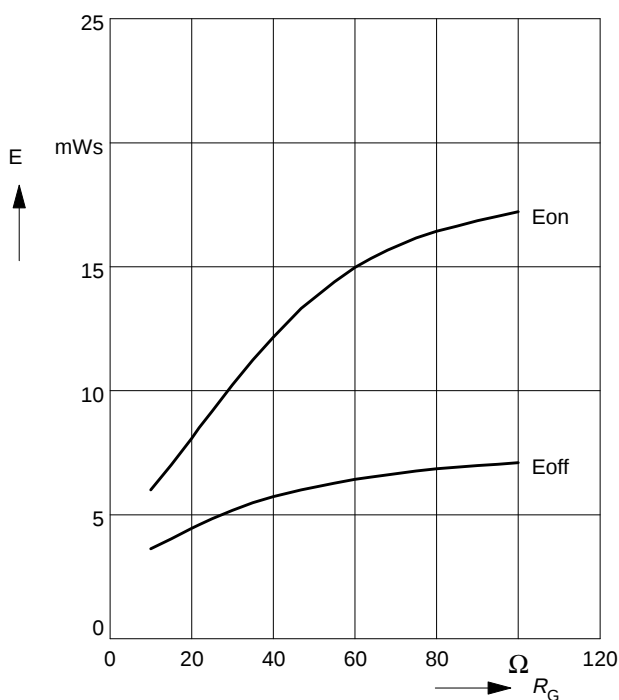
par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $R_G = 22\ \Omega$



### Typ. switching losses

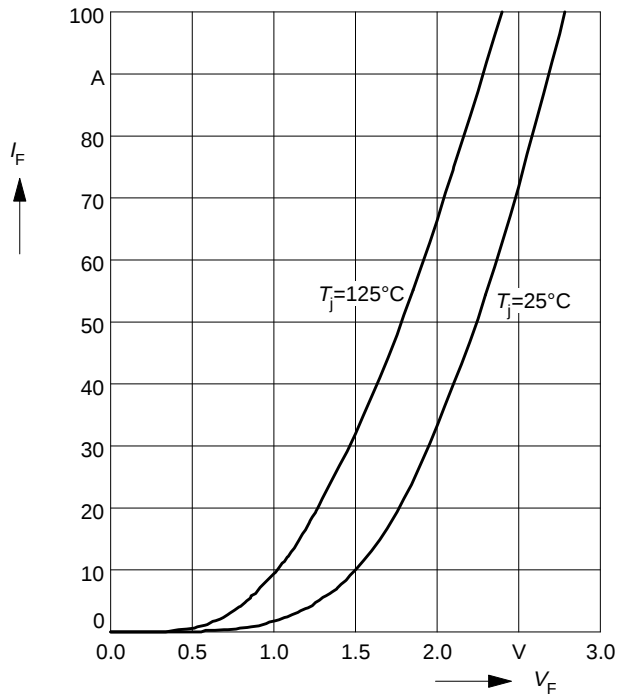
$E = f(R_G)$ , inductive load,  $T_j = 125^\circ\text{C}$

par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $I_C = 50\text{ A}$



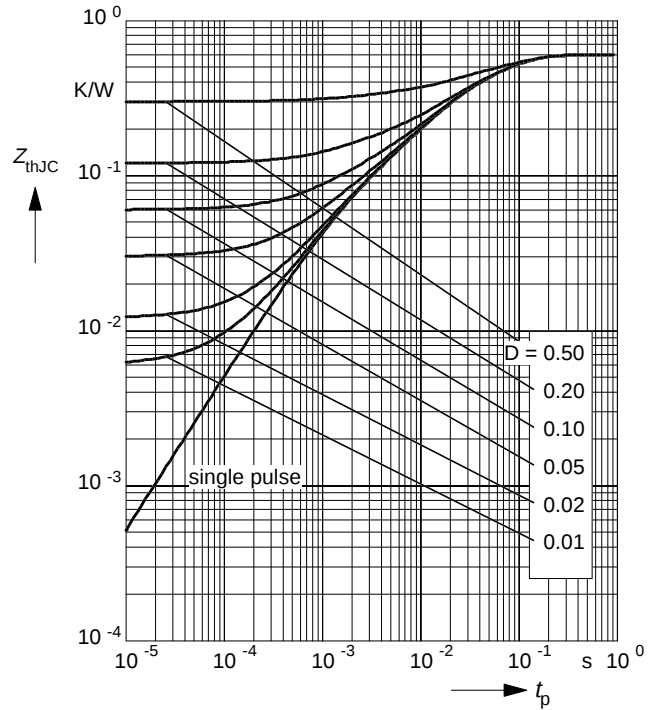
### Forward characteristics of fast recovery reverse diode $I_F = f(V_F)$

parameter:  $T_j$

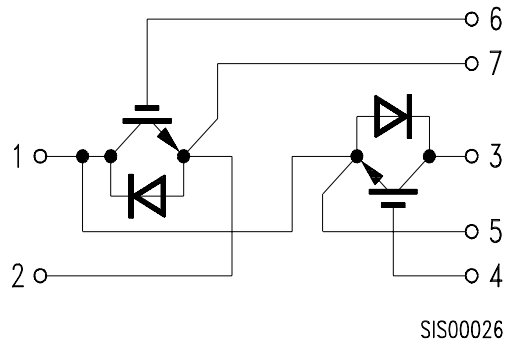


### Transient thermal impedance Diode $Z_{thJC} = f(t_p)$

parameter:  $D = t_p / T$



### Circuit Diagram



### Package Outlines

Dimensions in mm

Weight: 250 g

